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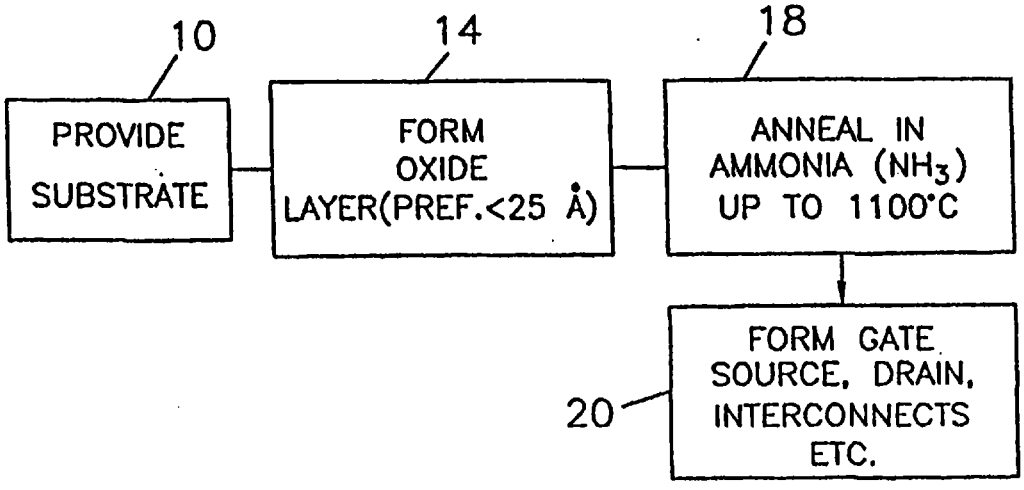


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(54) Title: METHOD FOR ESTABLISHING ULTRA-THIN GATE INSULATOR USING ANNEAL IN AMMONIA




WO 01/43177 A1

(57) Abstract: A method for fabricating a semiconductor device including a silicon substrate includes forming a thin Oxide base film on a substrate, and then annealing the substrate in ammonia. FET gates are then conventionally formed over the gate insulator. The resultant gate insulator is electrically insulative without degrading performance with respect to a conventioanal gate oxide insulator.